

Absolute Maximum Ratings

Voltage Between V+ and V- Terminals	36V
$\pm V_{SUPPLY}$ to Ground (V+, V-)	$\pm 18V$
V_R to Ground	$-V_{SUPPLY}$
V_L to Ground	$+V_{SUPPLY}$
Digital and Analog Input Voltage (V_A , V_S , V_D)	$+V_{SUPPLY} +4V$ $-V_{SUPPLY} -4V$
Peak Current (Source to Drain) (Pulse at 1ms, 10% Duty Cycle Max)	70mA
Continuous Current Any Pin	20mA
ESD Rating	<2000V

Thermal Information

Thermal Resistance	θ_{JA} ($^{\circ}C/W$)	θ_{JC} ($^{\circ}C/W$)
CerDIP Package	82	20
Package Power Dissipation at +75 $^{\circ}C$ CerDIP Package	1.0W	
Package Power Dissipation Derating Factor above +75 $^{\circ}C$ CerDIP Package12.3mW/ $^{\circ}C$	
Junction Temperature	+175 $^{\circ}C$	
Storage Temperature Range	-65 $^{\circ}C$ to +150 $^{\circ}C$	
Lead Temperature (Soldering 10s)	+300 $^{\circ}C$	

Recommended Operating Conditions

Operating Temperature Range	-55 $^{\circ}C$ to +125 $^{\circ}C$
Operating Supply Voltage Range	$\pm 15V$
Logic Supply Voltage (V_L)	+5.0V
Logic Reference Voltage (V_R)	0.0V
Analog Input Voltage (V_S)	$\pm V_{SUPPLY}$
Address Low Level (V_{AL})	0V to 0.8V
Address High Level (V_{AH})	2.4V to +5.0V

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

TABLE 1. D.C. ELECTRICAL PERFORMANCE SPECIFICATIONS

Device Tested at: Supply Voltage = $\pm 15V$, V_L = +5.0V, V_R = 0.0V, V_{AH} = 2.4V, V_{AL} = +0.8V, unused pins are grounded, unless otherwise specified.

D.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE ($^{\circ}C$)	MIN	MAX	UNITS
Switch "ON" Resistance	R_{DS2}	$V_D = -10V, I_S = 10mA$ S1/S2/S3/S4	1	+25	-	45	Ω
			2, 3	-55 to +125	-	50	Ω
		$V_D = 10V, I_S = -10mA$ S1/S2/S3/S4	1	+25	-	45	Ω
			2, 3	-55 to +125	-	50	Ω
Source "OFF" Leakage Current	$I_{S(OFF)}$	$V_S = -10V, V_D = 10V$ S1/S2/S3/S4	1	+25	-1	1	nA
			2, 3	-55 to +125	-100	100	nA
		$V_S = 10V, V_D = -10V$ S1/S2/S3/S4	1	+25	-1	1	nA
			2, 3	-55 to +125	-100	100	nA
Drain "OFF" Leakage Current	$I_{D(OFF)}$	$V_D = -10V, V_S = 10V$ S1/S2/S3/S4	1	+25	-1	1	nA
			2, 3	-55 to +125	-100	100	nA
		$V_D = 10V, V_S = -10V$ S1/S2/S3/S4	1	+25	-1	1	nA
			2, 3	-55 to +125	-100	100	nA
Channel "ON" Leakage Current	$I_{D(ON)}$	$V_D = V_S = 10V$ S1/S2/S3/S4	1	+25	-2	2	nA
			2, 3	-55 to +125	-200	200	nA
		$V_D = V_S = -10V$ S1/S2/S3/S4	1	+25	-2	2	nA
			2, 3	-55 to +125	-200	200	nA
Low Level Address Current	I_{AL}	$V_A = 0V$	1	+25	-1	1	μA
			2, 3	-55 to +125	-10	1	μA
High Level Address Current	I_{AH}	$V_A = 2.4V, 5V$	1	+25	-1	1	μA
			2, 3	-55 to +125	-1	10	μA
Positive Supply Current	$+I_{CC}$	$V_A = 0V, 5V$	1	+25	-	200	μA
			2, 3	-55 to +125	-	300	μA
Negative Supply Current	$-I_{CC}$	$V_A = 0V, 5V$	1	+25	-200	-	μA
			2, 3	-55 to +125	-300	-	μA

TABLE 1. D.C. ELECTRICAL PERFORMANCE SPECIFICATIONS (Continued)

Device Tested at: Supply Voltage = ±15V, V_L = +5.0V, V_R = 0.0V, V_{AH} = 2.4V, V_{AL} = +0.8V, unused pins are grounded, unless otherwise specified.

D.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE (°C)	MIN	MAX	UNITS
Logic Supply Current	+I _L	V _A = 0V, 5V	1	+25	-	200	µA
			2, 3	-55 to +125	-	300	µA
Reference Supply Current	+I _R	V _A = 0V, 5V	1	+25	-200	-	µA
			2, 3	-55 to +125	-300	-	µA

TABLE 2. A.C. ELECTRICAL PERFORMANCE SPECIFICATIONS

Device Tested at: Supply Voltage = ±15V, V_L = +5.0V, V_R = 0.0V, V_{AH} = +5.0V, V_{AL} = +0.0V, unused pins are grounded, unless otherwise specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE (°C)	MIN	MAX	UNITS
Turn "ON" Time	t _(ON)	V _S = 10V, -10V C _L = 10pF R _L = 1kΩ	11	-55	-	450	ns
			9	+25	-	500	ns
			10	+125	-	800	ns
Turn "OFF" Time	t _(OFF)	V _S = 10V, -10V C _L = 10pF R _L = 1kΩ	11	-55	-	350	ns
			9	+25	-	450	ns
			10	+125	-	600	ns

TABLE 3. ELECTRICAL PERFORMANCE SPECIFICATIONS (NOTE 1)

Device Characterized at: +V_{SUPPLY} = +15V, -V_{SUPPLY} = -15V, GND = 0V

PARAMETERS	SYMBOL	CONDITIONS	NOTE	TEMPERATURE (°C)	MIN	MAX	UNITS
"ON" Resistance Match (Channel to Channel)	r _{ON2} Match	V _D = ±10V I _D = 10mA	1	+25	-	10	Ω
Address Capacitance	C _A	V _A = 0V, 5V	1	+25	-	45	pF
Switch Input Capacitance	C _S (OFF)	Switch Off: V _A = 0V	1	+25	-	60	pF
Switch Output Capacitance	C _D (OFF)	Switch Off: V _A = 0V	1	+25	-	60	pF
	C _D (ON)	Switch On: V _A = 5V	1	+25	-	60	pF
Drain to Source Capacitance	C _{DS} (OFF)	Switch Off: V _A = 0V	1	+25	-	10	pF
Off Isolation	V _{ISO}	V _S = 2V _{P.P} @ f = 100kHz, R _L = 100Ω	1	+25	1	60	dB
Crosstalk	V _{CT}	V _S = 2V _{P.P} @ f = 100kHz, R _L = 100Ω	1	+25	1	60	dB
Charge Transfer Error	V _{CTE}	V _S = GND, C _L = 0.01µF V _A = 0V to 4V @ f = 200kHz	1	+25	-	30	mV

NOTE:

- Parameters listed in Table 3 are controlled via design or process parameters and are not directly tested at final production. These parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot to lot and within lot variation.

TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (Tables 1 and 2)
Interim Electrical Parameters (Pre Burn-in)	1
Final Electrical Test Parameters	1 (Note 2), 2, 3, 9, 10, 11
Group A Test Requirements	1, 2, 3, 9, 10, 11
Groups C & D Endpoints	1

NOTE:

- PDA applies to Subgroup 1 only.

Test Circuits

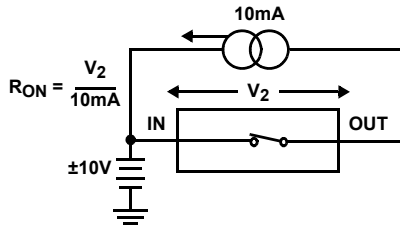


FIGURE 1. R_{DS}

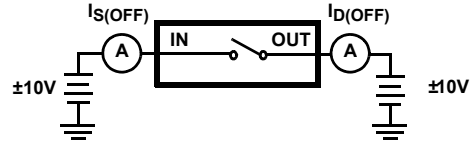


FIGURE 2. $I_{S(OFF)}$

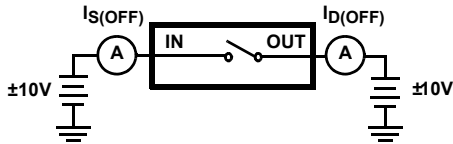


FIGURE 3. $I_{D(OFF)}$

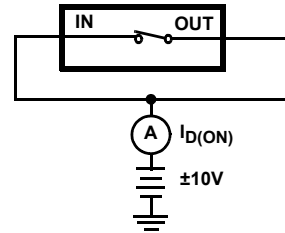


FIGURE 4. $I_{D(ON)}$

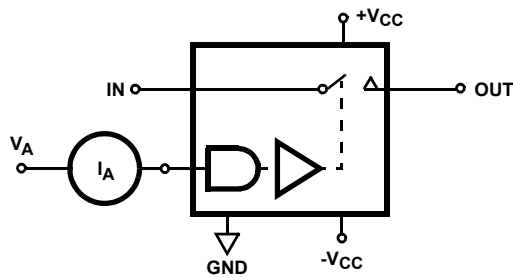


FIGURE 5. ADDRESS CURRENTS

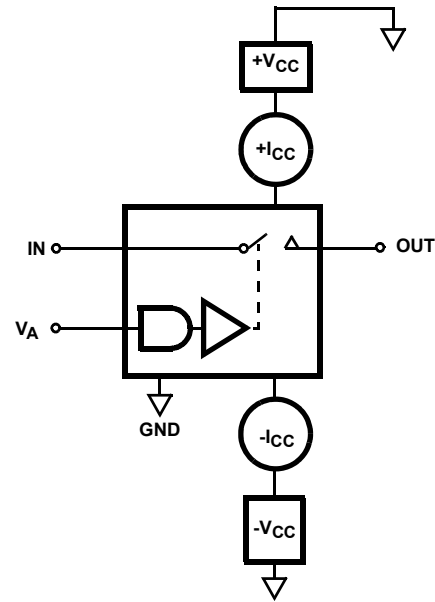


FIGURE 6. SUPPLY CURRENTS

Test Circuits (Continued)

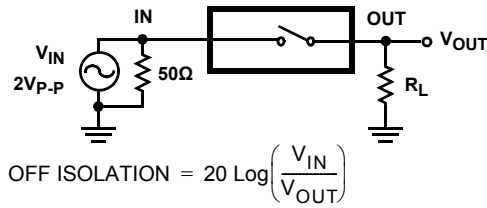
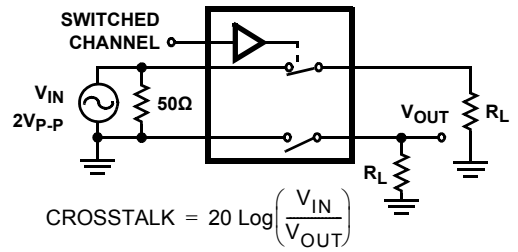
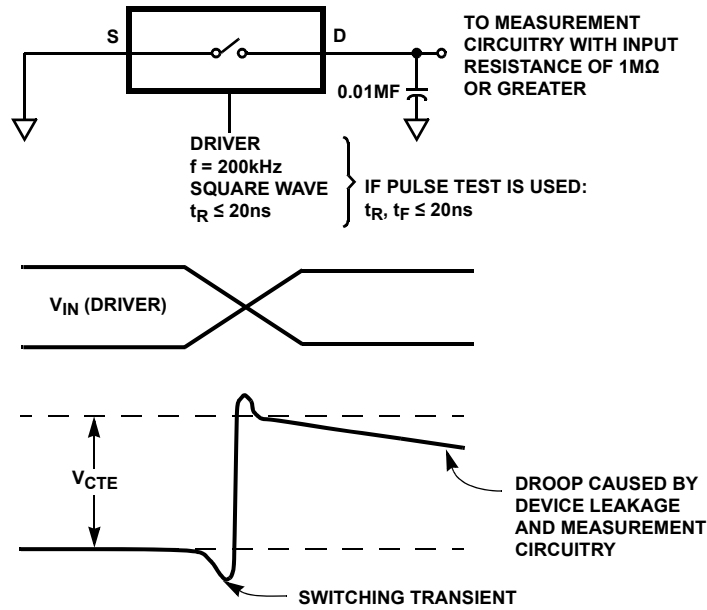


FIGURE 7. OFF ISOLATION



NOTE: Applies only to dual or double throw switches.

FIGURE 8. CROSSTALK



NOTE: V_{CTE} may be a positive or negative value.

FIGURE 9. CHARGE TRANSFER

Test Characteristics

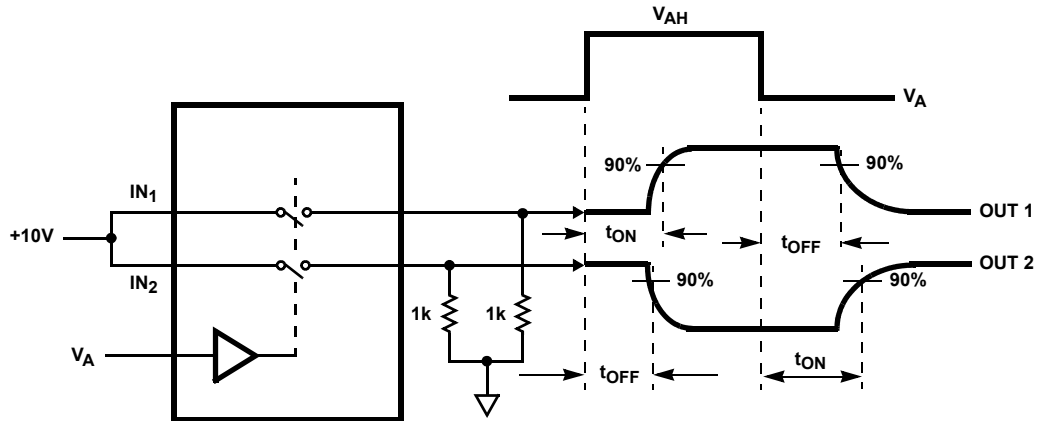


FIGURE 10. ON/OFF SWITCH TIME (t_{ON}, t_{OFF})

Test Characteristics (Continued)

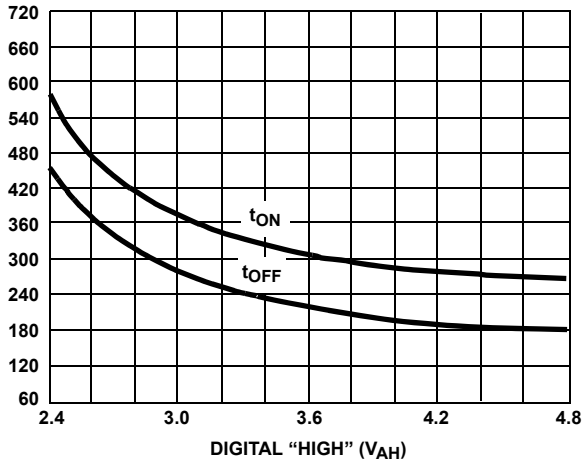


FIGURE 11. SWITCHING TIMES FOR DIGITAL TRANSITION

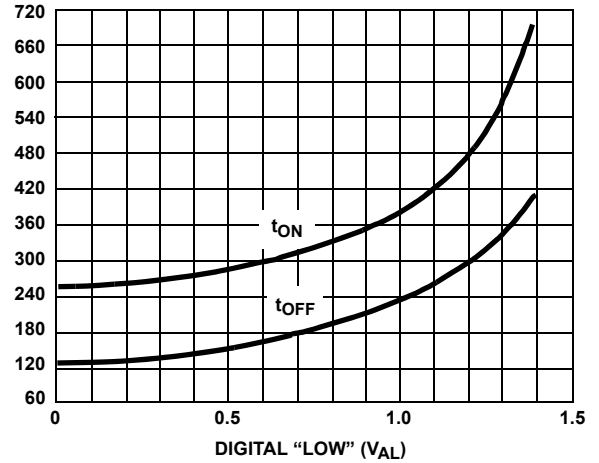
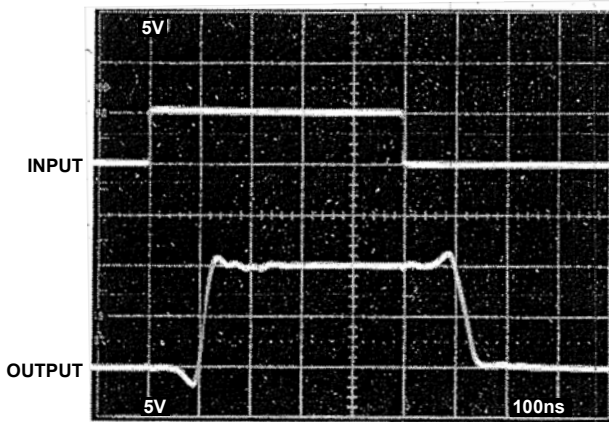


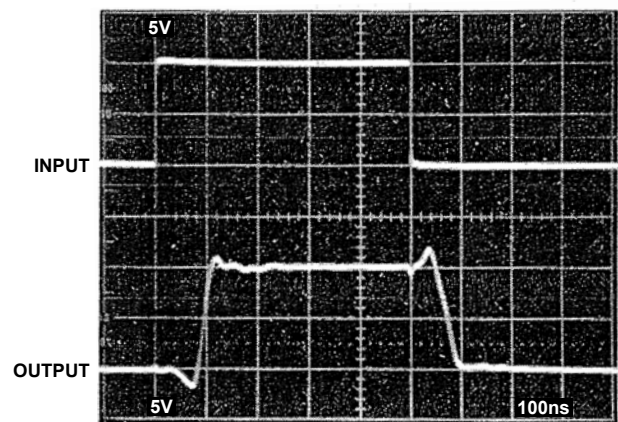
FIGURE 12. SWITCHING TIMES FOR NEGATIVE DIGITAL TRANSITION

Test Waveforms



Vertical Scale: Input = 5V/Div, (TTL; $V_{AH} = 5V$, $V_{AL} = 0V$)
 Output = 5V/Div
 Horizontal Scale: 100ns/Div

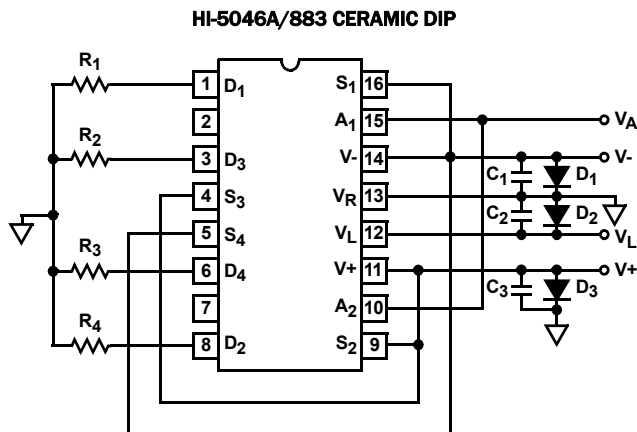
FIGURE 13.



Vertical Scale: Input = 5V/Div, (CMOS; $V_{AH} = 10V$, $V_{AL} = 0V$)
 Output = 5V/Div
 Horizontal Scale: 100ns/Div

FIGURE 14.

Burn-In Circuit



NOTES:

R_1 thru $R_4 = 10k\Omega, \pm 5\%, 1/4W$ (Min)

$C_1, C_2, C_3 = 0.01\mu F/\text{Socket}$ (Min) or $0.1\mu F/\text{Row}$, (Min)

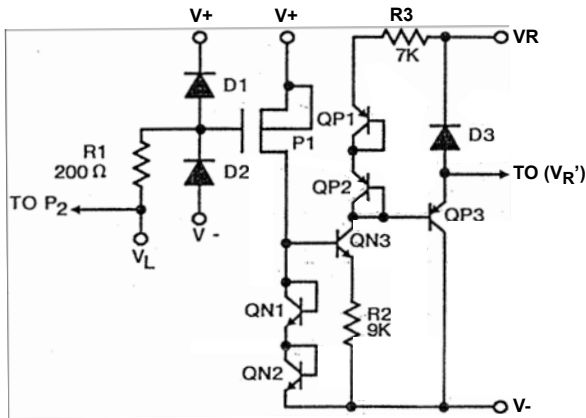
$D_1, D_2, D_3 = 1N4002$ or Equivalent/Board

$V_L = 5.5V \pm 0.5V$

$A_2 = A_2 = 5.5V \pm 0.5V$

$|(V+) - (V-)| = 30V$

Schematic Diagrams



NOTE: Connect V+ to V_L for minimizing power consumption when driving from CMOS circuits.

FIGURE 15. TTL/CMOS REFERENCE CIRCUIT

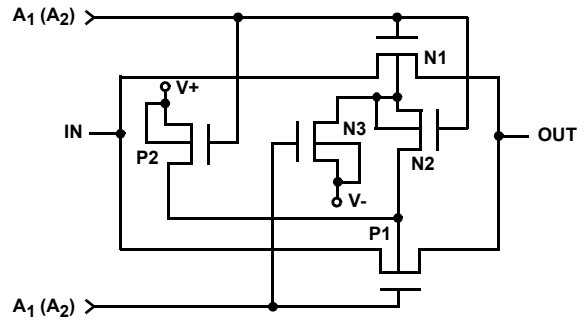
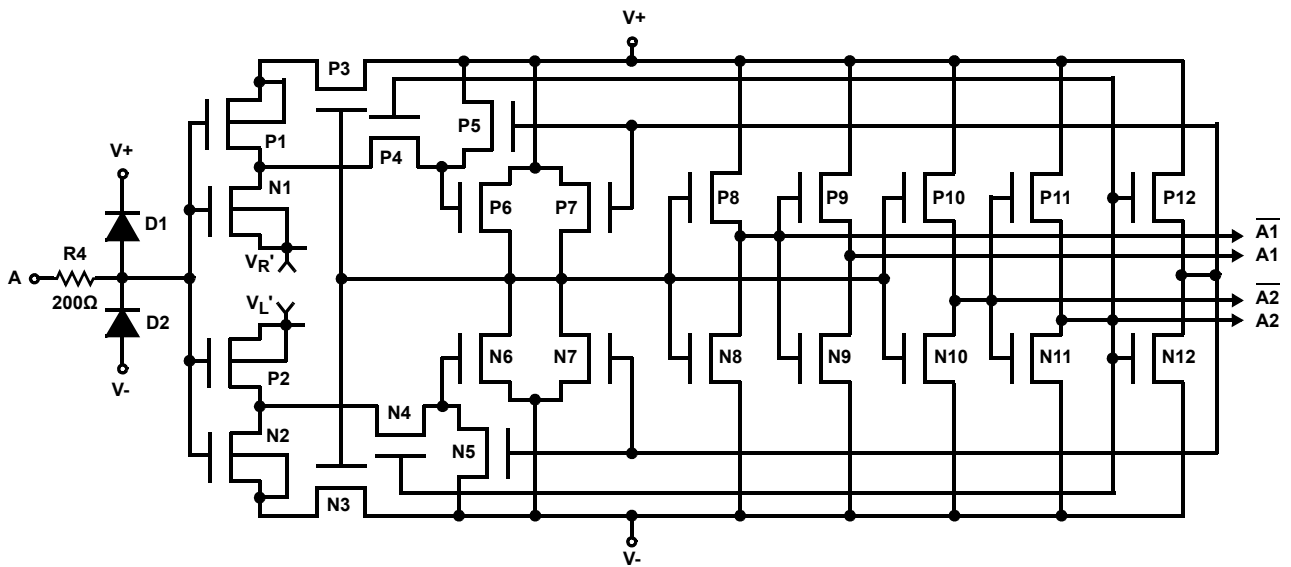


FIGURE 16. SWITCH CELL



All N-Channel bodies to V-, all P-Channel bodies to V+, except as shown.

DIGITAL INPUT BUFFER AND LEVEL SHIFTER

Die Characteristics

DIE DIMENSIONS:

96mils x 81mils x 19mils
 (2430µm x 2050µm x 480µm)

METALLIZATION:

Type: Aluminum
 Thickness: 16kÅ ±2kÅ

GLASSIVATION:

Type: Nitride over Silox
 Silox Thickness: 12kÅ ±2kÅ
 Nitride Thickness: 3.5kÅ ±1kÅ

SUBSTRATE POTENTIAL (Powered-up): V-

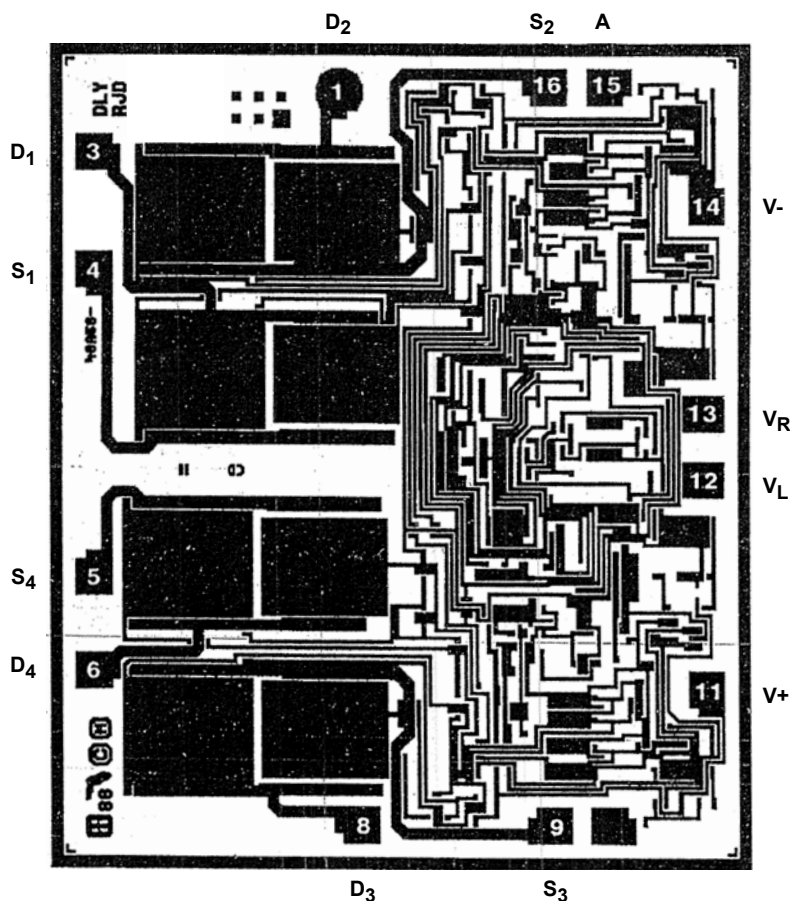
DEVICE COUNT: 82

WORST CASE CURRENT DENSITY:

1.0 x 10⁵A/cm² at 20mA

Metallization Mask Layout

HI-5046A/883



NOTE: Unused pins may be connected. Ground all unused pins.

Design Information The information contained in this section has been developed through characterization and is for use as application and design information only. No guarantee is implied.

Typical Performance Curves $T_A = +25^\circ\text{C}$, $V_{\text{SUPPLY}} = \pm 15\text{V}$

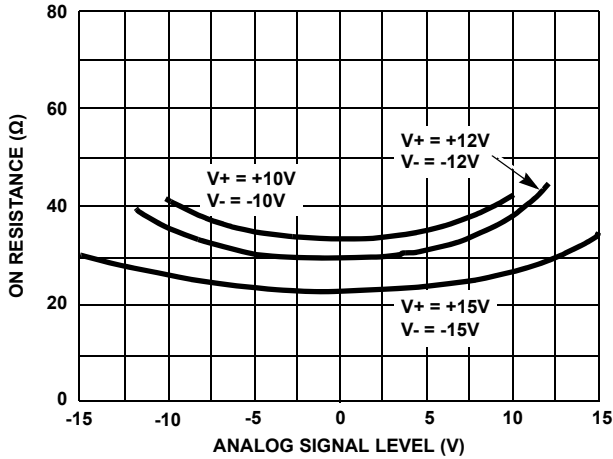


FIGURE 17. ON RESISTANCE vs ANALOG SIGNAL LEVEL AND POWER SUPPLY VOLTAGE

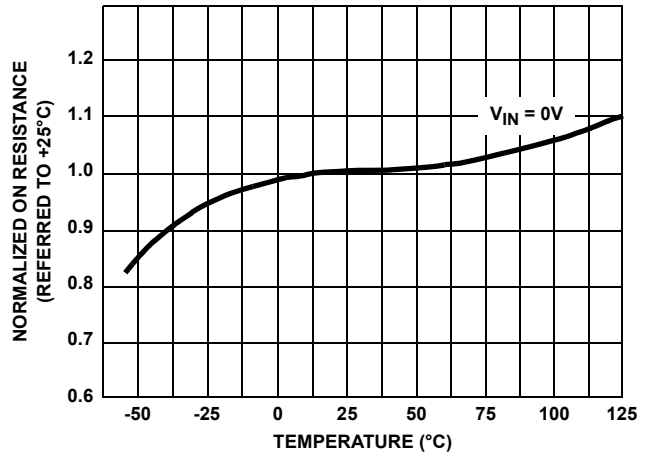


FIGURE 18. NORMALIZED ON RESISTANCE vs TEMPERATURE

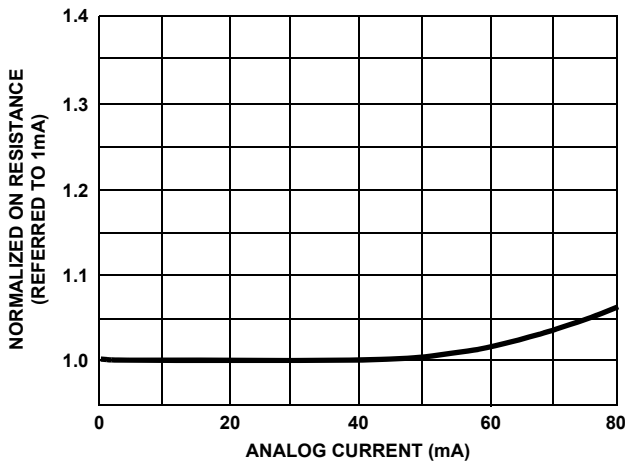


FIGURE 19. NORMALIZED ON RESISTANCE vs ANALOG CURRENT

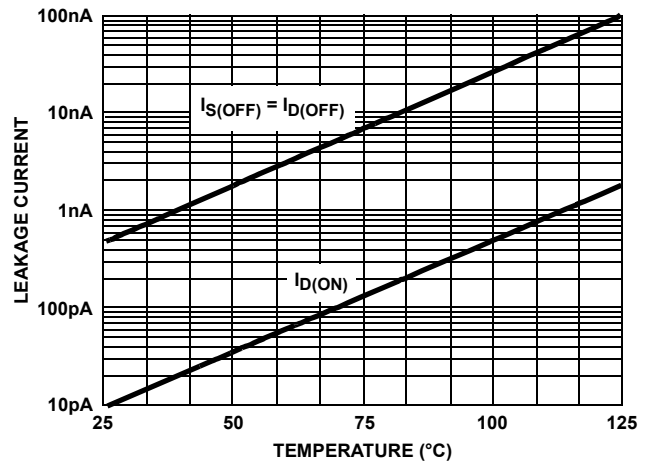


FIGURE 20. ON/OFF LEAKAGE CURRENTS vs TEMPERATURE

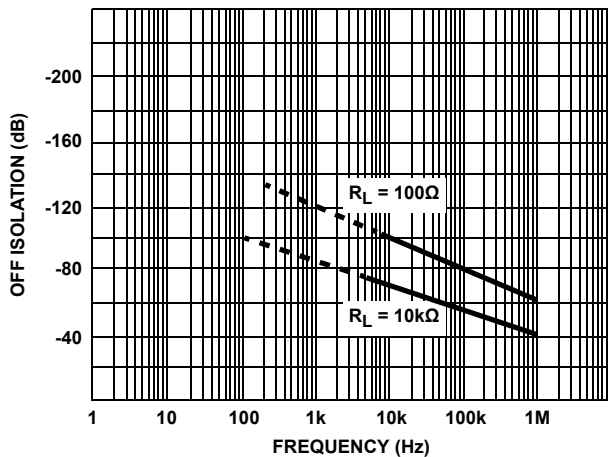


FIGURE 21. OFF ISOLATION vs FREQUENCY

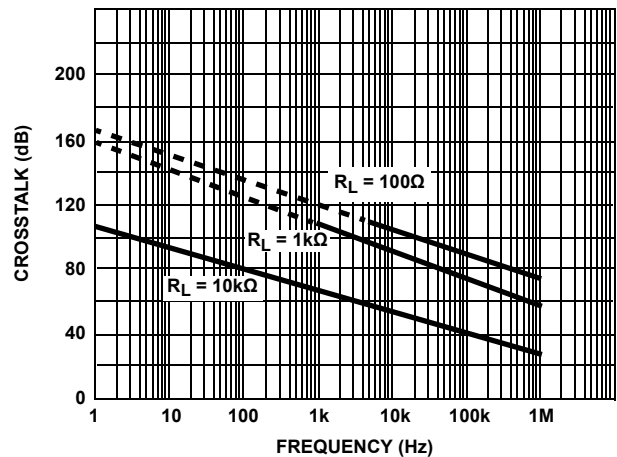


FIGURE 22. CROSSTALK vs FREQUENCY

Design Information The information contained in this section has been developed through characterization and is for use as application and design information only. No guarantee is implied.

Typical Performance Curves $T_A = +25^\circ\text{C}$, $V_{\text{SUPPLY}} = \pm 15\text{V}$ (Continued)

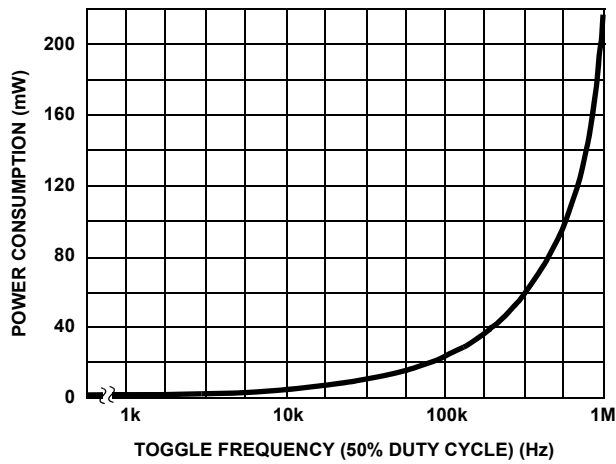
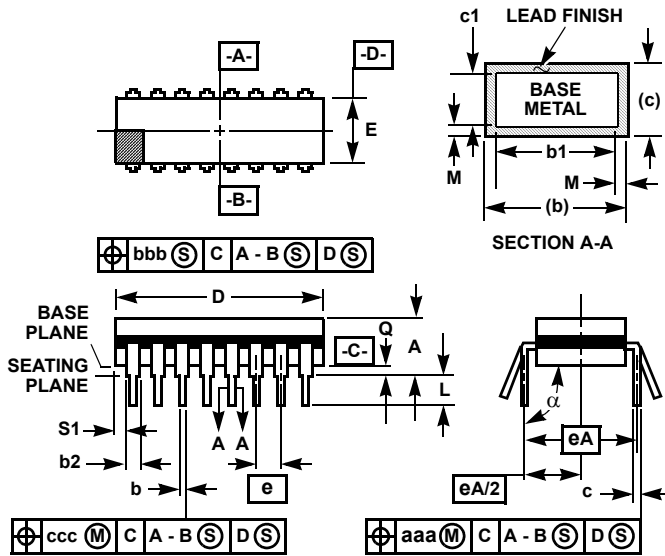


FIGURE 23. POWER CONSUMPTION vs FREQUENCY

Ceramic Dual-In-Line Frit Seal Packages (CERDIP)



**F16.3 MIL-STD-1835 GDIP1-T16 (D-2, CONFIGURATION A)
16 LEAD CERAMIC DUAL-IN-LINE FRIT SEAL PACKAGE**

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	-	0.200	-	5.08	-
b	0.014	0.026	0.36	0.66	2
b1	0.014	0.023	0.36	0.58	3
b2	0.045	0.065	1.14	1.65	-
b3	0.023	0.045	0.58	1.14	4
c	0.008	0.018	0.20	0.46	2
c1	0.008	0.015	0.20	0.38	3
D	-	0.840	-	21.34	5
E	0.220	0.310	5.59	7.87	5
e	0.100 BSC		2.54 BSC		-
eA	0.300 BSC		7.62 BSC		-
eA/2	0.150 BSC		3.81 BSC		-
L	0.125	0.200	3.18	5.08	-
Q	0.015	0.060	0.38	1.52	6
S1	0.005	-	0.13	-	7
α	90°	105°	90°	105°	-
aaa	-	0.015	-	0.38	-
bbb	-	0.030	-	0.76	-
ccc	-	0.010	-	0.25	-
M	-	0.0015	-	0.038	2, 3
N	16		16		8

NOTES:

1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
2. The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
3. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness.
4. Corner leads (1, N, N/2, and N/2+1) may be configured with a partial lead paddle. For this configuration dimension b3 replaces dimension b2.
5. This dimension allows for off-center lid, meniscus, and glass overrun.
6. Dimension Q shall be measured from the seating plane to the base plane.
7. Measure dimension S1 at all four corners.
8. N is the maximum number of terminal positions.
9. Dimensioning and tolerancing per ANSI Y14.5M - 1982.
10. Controlling dimension: INCH.

Rev. 0 4/94

© Copyright Intersil Americas LLC 1989-2012. All Rights Reserved.
All trademarks and registered trademarks are the property of their respective owners.

For additional products, see www.intersil.com/en/products.html

Intersil products are manufactured, assembled and tested utilizing ISO9001 quality systems as noted in the quality certifications found at www.intersil.com/en/support/qualandreliability.html

Intersil products are sold by description only. Intersil may modify the circuit design and/or specifications of products at any time without notice, provided that such modification does not, in Intersil's sole judgment, affect the form, fit or function of the product. Accordingly, the reader is cautioned to verify that datasheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see www.intersil.com

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Renesas Electronics:](#)

[HI1-5046A/883](#) [8100617EA/MLB](#)